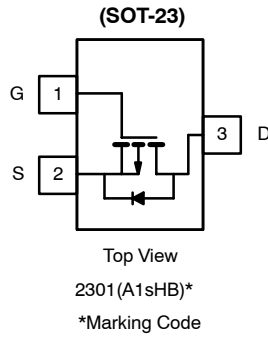


P-Channel AO2301MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.120 @ $V_{GS} = -4.5$ V	-2.3
	0.190 @ $V_{GS} = -2.5$ V	-1.8



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^b	I_D	$T_A = 25^\circ\text{C}$	-2.3
		$T_A = 70^\circ\text{C}$	-1.5
Pulsed Drain Current ^a	I_{DM}	-10	A
Continuous Source Current (Diode Conduction) ^b	I_S	-1.6	
Power Dissipation ^b	P_D	$T_A = 25^\circ\text{C}$	1.25
		$T_A = 70^\circ\text{C}$	0.8
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	100	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^c		166	

- Notes
- a. Pulse width limited by maximum junction temperature.
 - b. Surface Mounted on FR4 Board, $t \leq 5$ sec.
 - c. Surface Mounted on FR4 Board.